SOT23-6 P MOS

P-channel MOSFET in a SOT23-6 Plastic Package

V_{DS}(V)=-30V

I_D=-4.2A(V_{GS}=-10V)

RDS(ON)<50mΩ(VGS=-10V)

RDS(ON)<65mΩ(VGS=-4.5V)

This device is suitable for use as a load switch or in PWM applications.

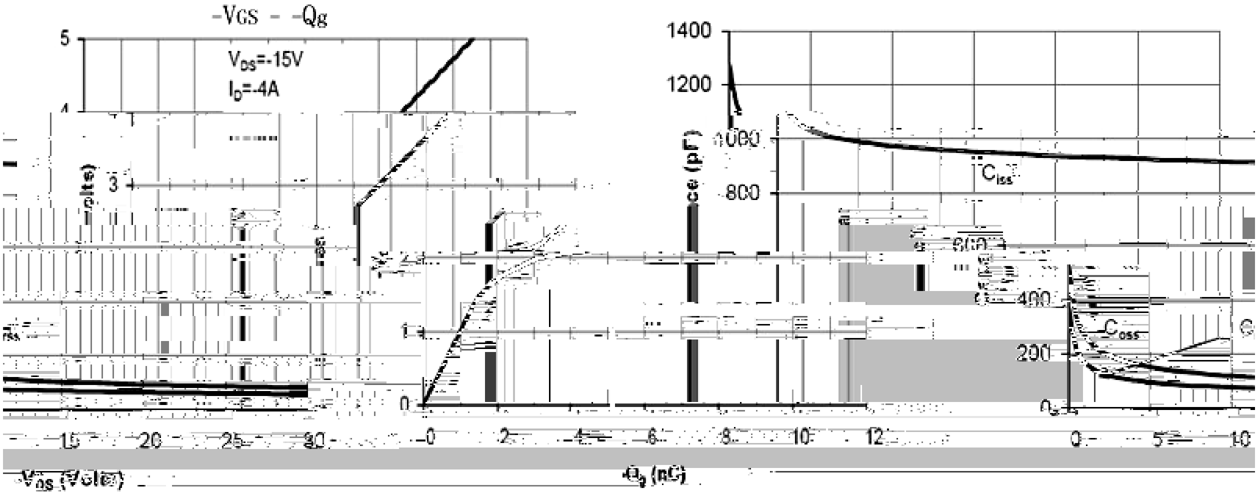
PIN1 D PIN 2 D PIN 3 G PIN 4 S PIN 5 D PIN 6 D

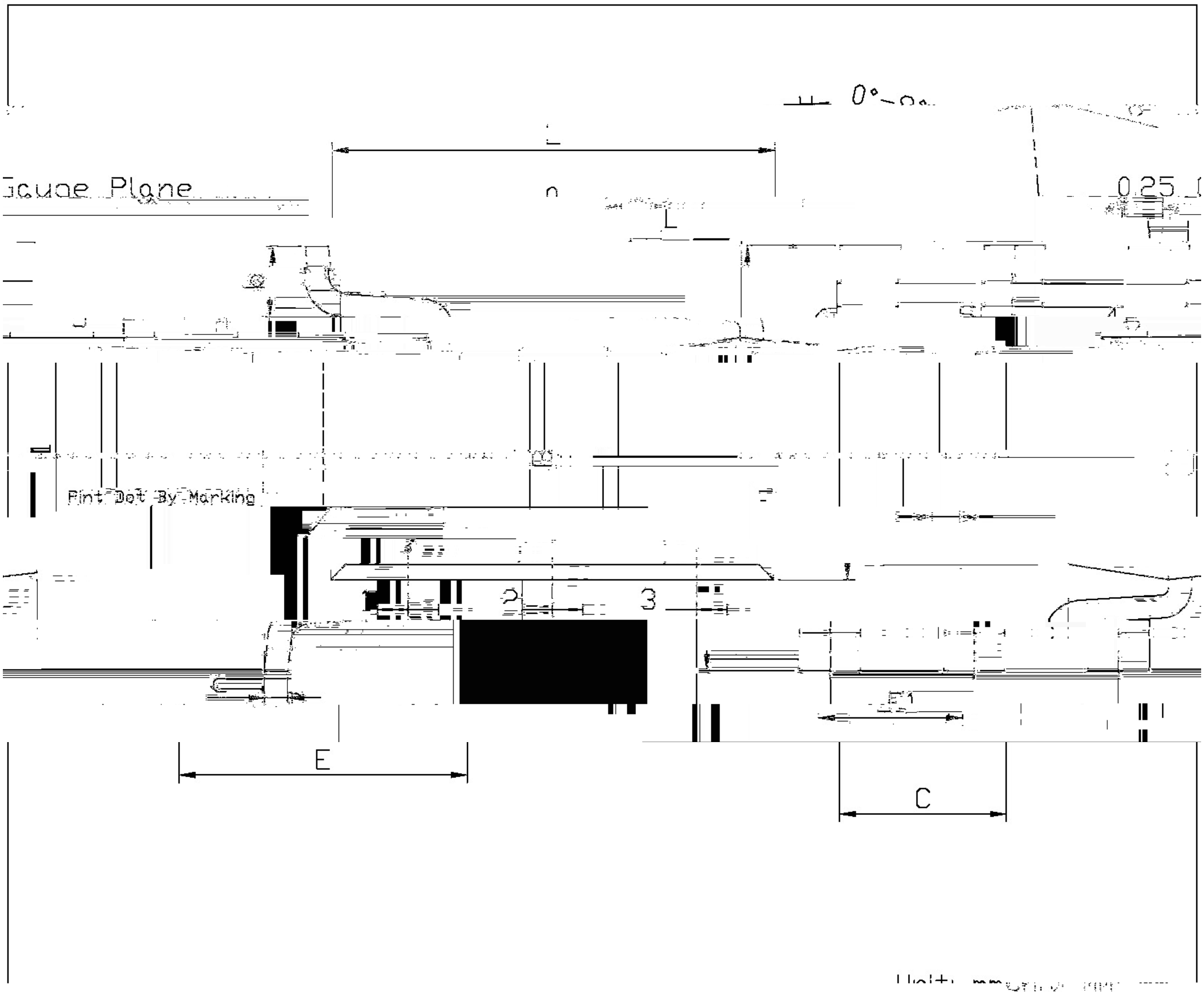
See Marking Instructions

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	-30	V
Drain Current – Continuous	$I_D(T_a=25\quad)$	-4.2	A
Drain Current- Continuous [A]	$I_D(T_a=70℃)$	-3.5	A
Pulsed Drain Current [B]	I_{DM}	-30	A
Gate-Source Voltage	V_{GS}	±12	V
Maximum Power Dissipation [A]	$P_D(T_a=25\quad)$	1.4	W
Total Power Dissipation [A]	$P_D(T_a=70℃)$	1.0	W
Maximum Junction-to-Ambient(Note 1)	$R_{\theta JA}$	125	/ W
Maximum Junction-to-Lead [C]	$R_{\theta JL}$	60	℃/W
Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ 150	℃

参数 Parameter	符□

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	V_{DS}=-15V V_{GS}=0V f=1MHz		957		pF


-VGS - -Qg
V_{DS}=-15V
I_D=-4A
5
4
3
2
1
0
0
2
4
6
8
10
12
-Q_g (nC)
1400
1200
1000
800
600
400
200
0
C_{iss}
C_{oss}
C_{rss}
0
5
10
15
20
25
30
-V_{DS} (Volts)



E1	2.60	3.00	[illegible]	0.35	0.55
E	1.80	2.00	[illegible]	[illegible]	0.15

SOT23-6